

German Gutierrez
Application No.: 09/650,275
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IN THE CLAIMS:

Please amend claim 1 as follows:

3uk
BC1

1. (Amended) A die seal structure for a semiconductor die having a
substrate comprising:
an elongate region electrically isolated from the remainder of the substrate
extending around a major portion of the periphery of the substrate and having a gap
between ends of the elongate region along a minor portion of the periphery; and
a conductive seal ring extending around the entire periphery of the die in
direct contact with the die throughout said elongate region in direct contact with and said
gap to provide a limited electrical connection between the ring and the substrate at said
gap.

Please cancel claims 9-13. ~~14~~.

B3
C1

14. (Amended) A die seal structure for a semiconductor die having a
substrate of a first conductivity type, comprising:
an elongate well region of a second conductivity type opposite from the
first conductivity type extending around a major portion of the periphery of the substrate
and having a gap between the ends of the elongate region along a minor portion of the
periphery; and
a conductive seal ring extending around the entire periphery of the die in
direct contact with the die throughout said elongate well region and in said gap to provide
a limited electrical connection between the ring and the substrate of said first
conductivity type at said gap.

B3 C2

18. (Amended) A semiconductor device comprising:
a. a die including a substrate;

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3 b. a die seal structure on the substrate, the structure comprising:
4 an elongate region electrically isolated from the remainder of the
5 substrate extending around a major portion of the periphery of the substrate and having a
6 gap between ends of the elongate region along a minor portion of the periphery; and
7 a conductive seal ring extending around the entire periphery of the die in
8 direct contact with the die throughout said elongate region and in direct contact with said
9 gap to provide a limited electrical connection between the ring and the substrate at said
10 gap.
